

### **In the Claims**

Claims 1-16 (cancelled).

Claim 17 (currently amended): The method of claim ~~16~~ 29 wherein the first and second monocrystalline materials consist essentially of silicon.

Claim 18 (currently amended): The method of claim ~~16~~ 29 wherein the first and second monocrystalline materials consist essentially of silicon, and wherein the insulative layer consists essentially of silicon dioxide.

Claim 19 (currently amended): The method of claim ~~16~~ 29 wherein the mask comprises a layer consisting essentially of silicon nitride over a layer consisting essentially of silicon dioxide.

Claims 20-27 (cancelled).

Claim 28 (currently amended): The method of claim ~~27~~ 29 wherein the anneal comprises maintaining the semiconductive material at a temperature of from about 800°C to about 1100°C for a time of from about 20 seconds to about 5 minutes, ~~and exposing the semiconductive material to laser light having a wavelength which interacts with one or more components of the semiconductive material.~~

Claim 29 (currently amended): ~~The method of claim 16~~ A method of forming semiconductor circuitry, comprising:

providing a substrate comprising a first monocrystalline material, an insulative layer over the first monocrystalline material, and a second monocrystalline material over the insulative layer and spaced from the first monocrystalline material by at least the insulative layer; the second monocrystalline material consisting essentially of a first element;

forming a mask to cover a first portion of the second monocrystalline material while leaving a second portion uncovered;

removing at least some of the uncovered portion to form a recess;

after forming the recess, forming an insulative material spacer along a sidewall of the recess;

after forming the insulative material spacer, entirely filling ~~wherein the~~

~~semiconductive material entirely fills the recess; wherein the~~ with a  
semiconductive material comprising at least 1 atomic percent of an element  
other than the first element, the semiconductive material ~~consists~~ consisting  
essentially of Si and Ge, with the Ge being present to an atomic  
concentration of from about 1% to about 20%, the semiconductive material  
being formed along the insulative material spacer; and the method further  
comprising:

chemical-mechanical polishing the semiconductive material to form a  
planarized surface which extends across the semiconductive material and  
mask;

after the chemical-mechanical polishing, exposing the semiconductive  
material to a laser to anneal the Si and Ge of the semiconductive material;  
and

~~the removing the mask occurring~~ after the anneal;

after removing the mask, forming a first semiconductor circuit  
component over the first portion of the second monocrystalline material; and  
forming a second semiconductor circuit component over the  
semiconductive material.

Claim 30 (original): The method of claim 29 wherein, after the removal of the mask, the semiconductive material extends above an uppermost surface of the first portion of the second monocrystalline substrate by a distance of from about 50Å to about 200Å.

Claims 31-56 (cancelled).

Claim 57 (new): The method of claim 29 wherein the first element is silicon.